

IN THE CLAIMS

1. (Currently Amended) A method for manufacturing a MRAM, comprising the steps of:

forming a metal layer for a connection layer connected to a semiconductor substrate through a lower insulating layer;

sequentially forming a pinned magnetic layer, a tunnel barrier layer and a free magnetic layer on the metal layer;

forming a hard mask on the free magnetic layer;

etching the hard mask layer and the free magnetic layer in a photolithography process using a MTJ cell mask to expose the tunnel barrier layer;

sequentially forming a barrier layer and an insulating film on the entire surface;

anisotropically etching the insulating film to form an insulating film spacer on a sidewall of the hard mask layer, and the free magnetic layer and the barrier layer; and

etching the tunnel barrier layer, the pinned magnetic layer and the metal layer using the insulating film spacer and the hard mask layer as a mask to form a MTJ cell and a connection layer.

2. (Original) The method according to claim 1, wherein the barrier layer is a TiN layer, a TiON layer or a Ta layer.

3. (Original) The method according to claim 1, wherein the insulating film is an oxide film or a nitride film.